Electronic Supplementary Information

Homoleptic gallium(III) and indium(III) aminoalkoxides as precursors for sol-gel routes to metal oxide nanomaterials

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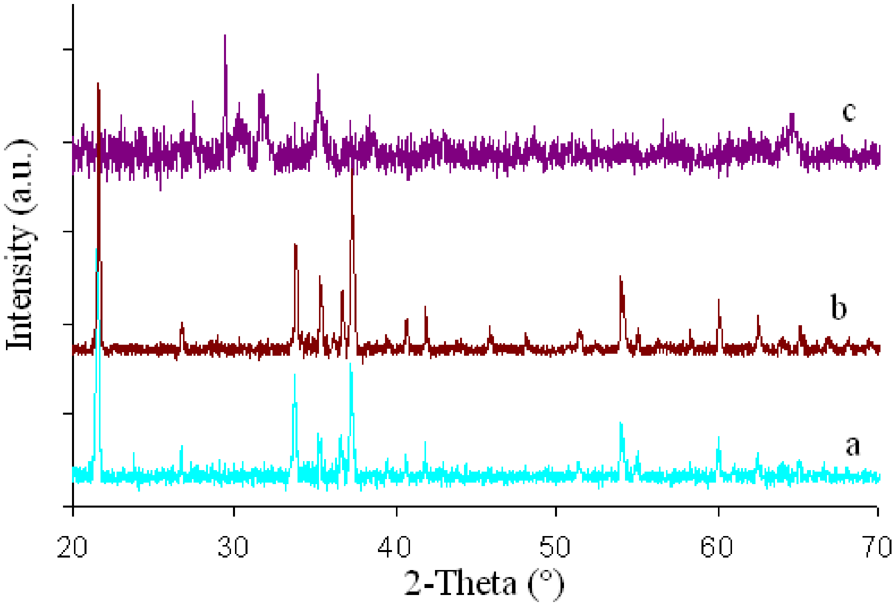

Fig. S1: XRD patterns of powders obtained after hydrolysis of **3**: (a) as-prepared, (b) as-prepared in presence of NR_4Br, and (c) calcined at 500 °C.

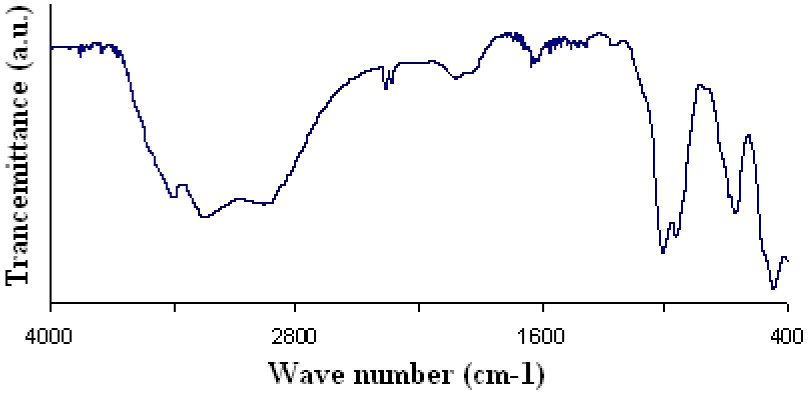

Fig. S2: FT-IR spectrum of as-prepared powder obtained after hydrolysis of $Ga(OPr^{i})_3$

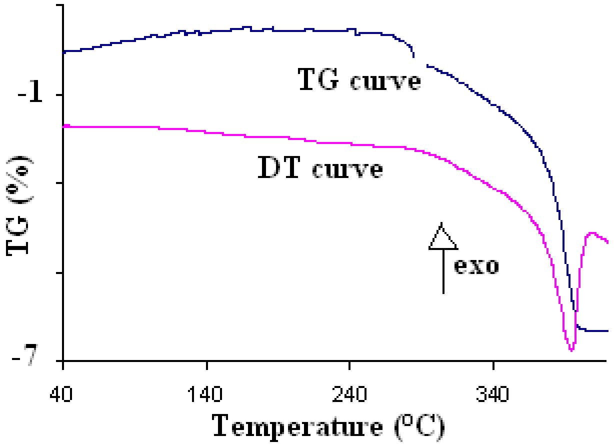

Fig S3. TG-DTA curves of as-prepared powder obtained after hydrolysis of $Ga(OPr^{i})_3$

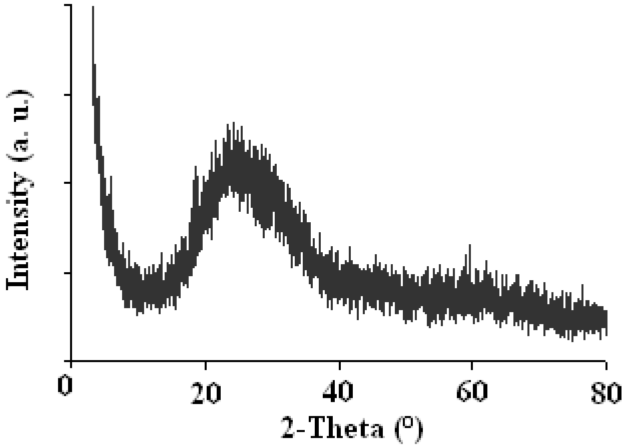

Fig S4. XRD of Ga_2O_3 film on glass obtained from **1** and calcined at 500 °C for 4 hrs.

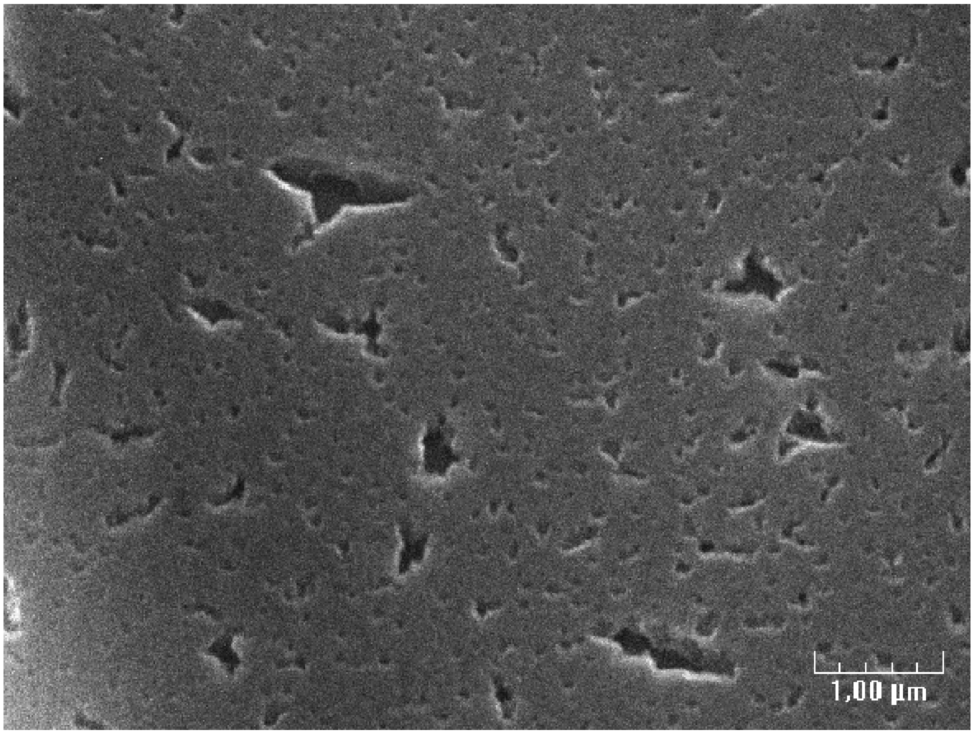

Fig S5: SEM images of Ga_2O_3 films obtained from **1** on glass slide.

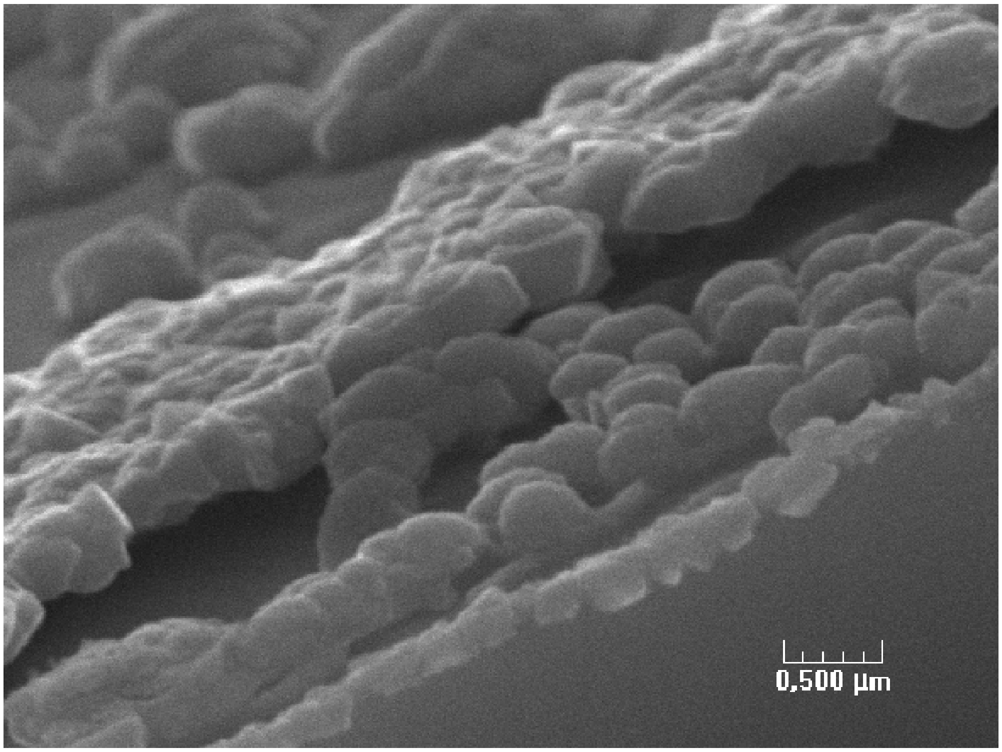

Fig S6: SEM images of In_2O_3 film obtained from **2** on Si wafer.